

Notice of References Cited	Application/Control No. 10/784,947		Applicant(s)/Patent Under Reexamination TOTSUKA ET AL.	
	Examiner Bac H. Au		Art Unit 2822	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,592,771	07-2003	Yamanaka et al.	216/63
	B	US-			
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	D	US-			
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	F	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Spruytte, Sylvia G.; MBE Growth on Nitride-Arsenide Materials for Long Wavelength Optoelectronics; 3 December 1999; MRS Internet J. Nitride Semicond. Res. 5S1, W8.4 (2000).
	V	Vaudo, R. P.; Atomic-nitrogen production in a radio-frequency plasma source; 1 November 1993; Optical Society of America, Optics Letter; Vol.18, No.21.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.